

Chopper Stabilized Precision Hall Effect Switches

Features and Benefits

- Unipolar switchpoints
- Resistant to physical stress
- Superior temperature stability
- Output short-circuit protection
- Operation from unregulated supply
- Reverse battery protection
- Solid-state reliability
- Small package sizes

Packages:



Not to scale

Description

The A1120 and A1125 Hall-effect, unipolar switches are extremely temperature-stable and stress-resistant sensor ICs, especially suited for operation over extended temperature ranges to 150°C. Superior high-temperature performance is made possible through dynamic offset cancellation, which reduces the residual offset voltage normally caused by device overmolding, temperature dependencies, and thermal stress.

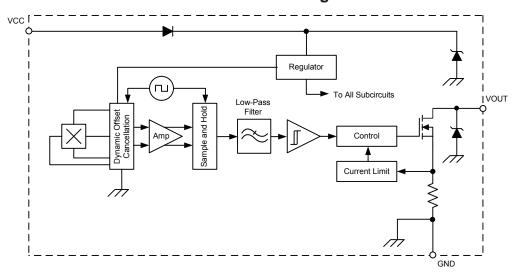
Each device includes on a single silicon chip a voltage regulator, Hall-voltage generator, small-signal amplifier, chopper stabilization, Schmitt trigger, and a short-circuit protected open-collector output to sink up to 25 mA.

An on-board regulator permits operation with supply voltages of 3 to 24 V. The advantage of operating down to 3 V is that the device can be used in 3 V applications or with additional external resistance in series with the supply pin for greater protection against high voltage transient events.

For the A1120, a south pole of sufficient strength turns the output on. Removal of the magnetic field turns the output off. The A1125 is complementary to the A1120 in that, for the A1125, a south pole turns the output off, and removal of the magnetic field turns the output on.

Two package styles provide a magnetically optimized package for most applications. Package type LH is a modified SOT23W, surface mount package, while UA is a three-lead ultra-mini SIP for through-hole mounting. Each package type is lead (Pb) free (suffix, -T), with a 100% matter tin plated leadframe.

Functional Block Diagram



A1120 and A1120 and A1120 A112

Selection Guide

Part Number	Packing ¹	Mounting	Ambient, T _A	Output In South (Positive) Magnetic Field	
A1120ELHLX-T	13-in. reel, 10000 pieces/reel	3-pin SOT23W surface mount			
A1120ELHLT-T ²	7-in. reel, 3000 pieces/reel	3-pin SOT23W surface mount	-40°C to 85°C		
A1120EUA-T	Bulk, 500 pieces/bag	3-pin SIP through hole		On (logic low)	
A1120LLHLX-T	13-in. reel, 10000 pieces/reel	3-pin SOT23W surface mount		On (logic low)	
A1120LLHLT-T ²	7-in. reel, 3000 pieces/reel	3-pin SOT23W surface mount	-40°C to 150°C		
A1120LUA-T	Bulk, 500 pieces/bag	3-pin SIP through hole			
A1125ELHLX-T	13-in. reel, 10000 pieces/reel	3-pin SOT23W surface mount	-40°C to 85°C		
A1125EUA-T	Bulk, 500 pieces/bag	3-pin SIP through hole	-40°C (0 65°C	Off (logic bigh)	
A1125LLHLX-T	13-in. reel, 10000 pieces/reel	3-pin SOT23W surface mount	400C to 4500C	Off (logic high)	
A1125LUA-T	Bulk, 500 pieces/bag	3-pin SIP through hole	-40°C to 150°C		

^{*}Contact Allegro for additional packing options.

Absolute Maximum Ratings

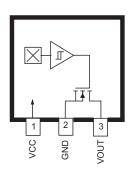
Characteristic	Symbol	Notes	Rating	Units	
Forward Supply Voltage	V _{CC}		26.5	V	
Reverse Supply Voltage	V _{RCC}		-30	V	
Output Off Voltage	V _{OUT}		26	V	
Continuous Output Current	I _{OUT}		25	mA	
Reverse Output Current	I _{ROUT}		-50	mA	
Operating Ambient Temperature	т.	Range E	-40 to 85	°C	
Operating Ambient Temperature T _A		Range L	-40 to 150	°C	
Maximum Junction Temperature	T _J (max)		165	°C	
Storage Temperature	T _{stg}		-65 to 170	°C	



Pin-out Diagrams

Package LH

Package UA



Terminal List

Name	Description	Number		
Name	Description	Package LH	Package UA	
VCC	Connects power supply to chip	1	1	
VOUT	Output from circuit	2	3	
GND	Ground	3	2	



²Available through authorized Allegro distributors only.

A1120 and A1120 LHLT-T" ** Precision Hall Effect Switches A1125

ELECTRICAL CHARACTERISTICS Valid valid over full operating voltage and ambient temperature ranges; unless otherwise noted

Characteristics	Symbol	Test Conditions		Min.	Typ.1	Max.	Unit ²
Electrical Characteristics				1			
Forward Supply Voltage	V _{CC}	Operating, T _J < 165°C		3	_	24	V
Outside a language		A1120	V _{OUT} = 24 V, B < B _{RP}	_	_	10	μΑ
Output Leakage Current	loutoff	A1125	V _{OUT} = 24 V, B > B _{OP}	_	_	10	μΑ
Outside Outside State Vallage	.,	A1120	I _{OUT} = 20 mA, B > B _{OP}	_	185	500	mV
Output Saturation Voltage	V _{OUT(SAT)}	A1125	I _{OUT} = 20 mA, B < B _{RP}	_	185	500	mV
0.4.4.0		A1120	B > B _{OP}	30	_	60	mA
Output Current Limit	Іом	A1125	B < B _{RP}	30	- 24 - 10 - 10 185 500 185 500	mA	
Power-On Time ³	t _{PO}	V _{CC} > 3.0 B > B _{OP} ($V_{CC} > 3.0 \text{ V, B} < B_{RP}(\text{min}) - 10 \text{ G,}$ $V_{CC} > 3.0 \text{ V, B} < B_{RP}(\text{min}) = 10 \text{ G,}$		_	25	μs
Chopping Frequency	f _C			_	800	_	kHz
Output Rise Time ^{3,4}	t _r	R _L = 820 Ω, C _S = 20 pF		_	0.2	2	μs
Output Fall Time ^{3,4}	t _f	R _L = 820 Ω, C _S = 20 pF		_	0.1	2	μs
·		A1120	V _{CC} = 12 V, B > B _{OP}	_	_	4	mA
	I _{CC(ON)}	A1125	V _{CC} = 12 V, B < B _{RP}	B > B _{OP} - 4 B < B _{RP} - 4 B < B _{RP} - 4	mA		
Supply Current		A1120	V _{CC} = 12 V, B < B _{RP}	_	_	4	mA
	I _{CC(OFF)}	A1125	V _{CC} = 12 V, B > B _{OP}	_	_	4	mA
Reverse Supply Current	I _{RCC}	A1125 $V_{CC} = 12 \text{ V, B} > B_{OP}$ $V_{RCC} = -30 \text{ V}$ $I_{CC} = 5 \text{ mA; } T_A = 25^{\circ}\text{C}$		_	_	-5	mA
Supply Zener Clamp Voltage	V _Z	I _{CC} = 5 m	nA; T _A = 25°C	28	_	_	V
Zener Impedance	I _Z	I _{CC} = 5 m	nA; T _A = 25°C	_	50	_	Ω
Magnetic Characteristics							
On annuta Daint	B _{OP}	A1120		_	35	50	G
Operate Point		A1125		_	35	50	G
Deleges Deint	В	A1120		5	25	_	G
Release Point	B _{RP}	A1125		5	25	_	G
Hysteresis	B _{HYS}	(B _{OP} – B	RP)	_	10	_	G

 $^{^{1}}$ Typical data are are at T_A = 25 $^{\circ}$ C and V_{CC} = 12 V, and are for initial design estimations only.



²1 G (gauss) = 0.1 mT (millitesla).

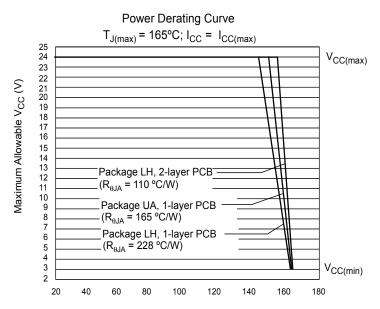
³Guaranteed by device design and characterization.

 $^{{}^{4}}C_{S}$ = oscilloscope probe capacitance.

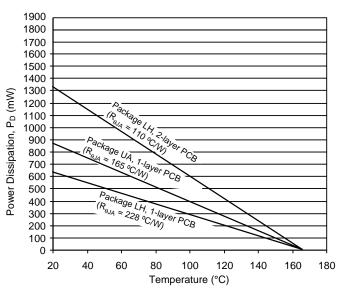
A1120 and A1120 A1120 A1120 A1120 A1120 A1125 Precision Hall Effect Switches

THERMAL CHARACTERISTICS may require derating at maximum conditions, see application information

Characteristic	Symbol	Test Conditions		Units
Package Thermal Resistance	$R_{ heta JA}$	Package LH, 1-layer PCB with copper limited to solder pads		°C/W
		Package LH, 2-layer PCB with 0.463 in 2 of copper area each side connected by thermal vias	110	°C/W
		Package UA, 1-layer PCB with copper limited to solder pads	165	°C/W



Power Dissipation versus Ambient Temperature





4

Functional Description

Operation

The output of the A1120 devices switches low (turns on) when a magnetic field perpendicular to the Hall element exceeds the operate point threshold, B_{OP} (see panel A of figure 1). When the magnetic field is reduced below the release point, B_{RP} , the device output goes high (turns off). The output of the A1125 devices switches high (turns off) when a magnetic field perpendicular to the Hall element exceeds the operate point threshold, B_{OP} (see panel B of figure 1). When the magnetic field is reduced below the release point, B_{RP} , the device output goes low (turns on).

After turn-on, the output voltage is $V_{OUT(SAT)}$. The output transistor is capable of sinking current up to the short circuit current limit, I_{OM} , which is a minimum of 30 mA.

The difference in the magnetic operate and release points is the hysteresis, B_{HYS} , of the device. This built-in hysteresis allows clean switching of the output even in the presence of external mechanical vibration and electrical noise. Powering-on the device in the hysteresis range (less than B_{OP} and higher than B_{RP}) will

give an indeterminate output state. The correct state is attained after the first excursion beyond B_{OP} or B_{RP} .

Applications

It is strongly recommended that an external bypass capacitor be connected (in close proximity to the Hall element) between the supply and ground of the device to reduce external noise in the application. As is shown in panel B of figure 1, a 0.1 μF capacitor is typical.

Extensive applications information for Hall effect devicers is available in:

- Hall-Effect IC Applications Guide, Application Note 27701
- Guidelines for Designing Subassemblies Using Hall-Effect Devices, Application Note 27703.1
- Soldering Methods for Allegro's Products SMT and Through-Hole, Application Note 26009

All are provided in *Allegro Electronic Data Book*, AMS-702, and the Allegro Web site, www.allegromicro.com.

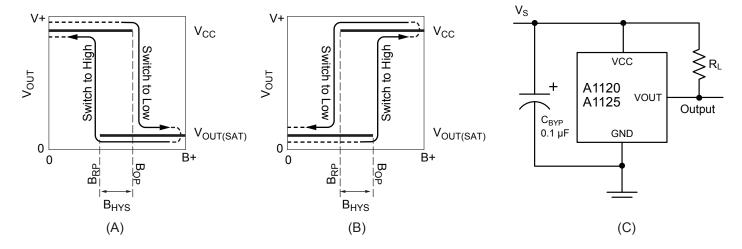


Figure 1. Device switching behavior. In panels A and B, on the horizontal axis, the B+ direction indicates increasing south polarity magnetic field strength. This behavior can be exhibited when using an electrical circuit such as that shown in panel C.



A1120 and A1120 LLHLT-T" A1120LLHLT-T" A1120

Chopper Stabilization Technique

When using Hall effect technology, a limiting factor for switchpoint accuracy is the small signal voltage developed across the Hall element. This voltage is disproportionally small relative to the offset that can be produced at the output of the Hall element. This makes it difficult to process the signal while maintaining an accurate, reliable output over the specified operating temperature and voltage ranges.

Chopper stabilization is a unique approach used to minimize Hall offset on the chip. The patented Allegro technique, namely Dynamic Quadrature Offset Cancellation, removes key sources of the output drift induced by thermal and mechanical stresses. This offset reduction technique is based on a signal modulation-demodulation process. The undesired offset signal is separated from the magnetic field-induced signal in the frequency domain, through modulation. The subsequent demodulation acts as a modulation process for the offset, causing the magnetic field induced signal to recover its original spectrum at baseband, while the dc offset becomes a high-frequency signal. The magnetic sourced signal then can pass through a low-pass filter, while the modulated DC offset is suppressed. This configuration is illustrated in figure 2.

The chopper stabilization technique uses a 400 kHz high frequency clock. For demodulation process, a sample and hold technique is used, where the sampling is performed at twice the chopper frequency (800 kHz). This high-frequency operation allows a greater sampling rate, which results in higher accuracy and faster signal-processing capability. This approach desensitizes the chip to the effects of thermal and mechanical stresses, and produces devices that have extremely stable quiescent Hall output voltages and precise recoverability after temperature cycling. This technique is made possible through the use of a BiCMOS process, which allows the use of low-offset, low-noise amplifiers in combination with high-density logic integration and sample-and-hold circuits.

The repeatability of magnetic field-induced switching is affected slightly by a chopper technique. However, the Allegro high frequency chopping approach minimizes the affect of jitter and makes it imperceptible in most applications. Applications that are more likely to be sensitive to such degradation are those requiring precise sensing of alternating magnetic fields; for example, speed sensing of ring-magnet targets. For such applications, Allegro recommends its digital device families with lower sensitivity to jitter. For more information on those devices, contact your Allegro sales representative.

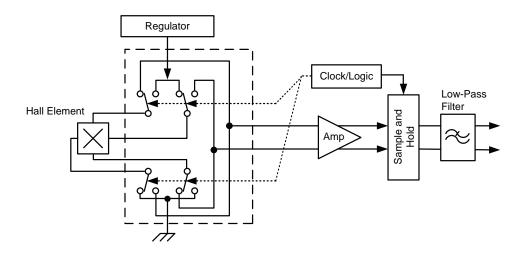


Figure 2. Model of chopper stabilization technique



A1120 and A1120 LLHLT-T" (Example of Stabilized Precision Hall Effect Switches

Power Derating

The device must be operated below the maximum junction temperature of the device, $T_{J(max)}$. Under certain combinations of peak conditions, reliable operation may require derating supplied power or improving the heat dissipation properties of the application. This section presents a procedure for correlating factors affecting operating T_J . (Thermal data is also available on the Allegro MicroSystems website.)

The Package Thermal Resistance, $R_{\theta JA}$, is a figure of merit summarizing the ability of the application and the device to dissipate heat from the junction (die), through all paths to the ambient air. Its primary component is the Effective Thermal Conductivity, K, of the printed circuit board, including adjacent devices and traces. Radiation from the die through the device case, $R_{\theta JC}$, is relatively small component of $R_{\theta JA}$. Ambient air temperature, T_A , and air motion are significant external factors, damped by overmolding.

The effect of varying power levels (Power Dissipation, P_D), can be estimated. The following formulas represent the fundamental relationships used to estimate T_J , at P_D .

$$P_D = V_{IN} \times I_{IN} \tag{1}$$

$$\Delta T = P_D \times R_{\theta IA} \tag{2}$$

$$T_{J} = T_{A} + \Delta T \tag{3}$$

For example, given common conditions such as: T_A = 25°C, V_{CC} = 12 V, I_{CC} = 1.6 mA, and $R_{\theta JA}$ = 165 °C/W, then:

$$P_D = V_{CC} \times I_{CC} = 12 \text{ V} \times 1.6 \text{ mA} = 19 \text{ mW}$$

$$\Delta T = P_D \times R_{\theta JA} = 19 \text{ mW} \times 165 \text{ °C/W} = 3 \text{ °C}$$

$$T_{I} = T_{\Delta} + \Delta T = 25^{\circ}C + 3^{\circ}C = 28^{\circ}C$$

A worst-case estimate, $P_{D(max)}$, represents the maximum allowable power level ($V_{CC(max)}$, $I_{CC(max)}$), without exceeding $T_{J(max)}$, at a selected $R_{\theta JA}$ and T_A .

Example: Reliability for V_{CC} at T_A=150°C, package LH, using a minimum-K PCB.

Observe the worst-case ratings for the device, specifically: $R_{\theta JA} = 228^{\circ}\text{C/W}$, $T_{J}(\text{max}) = 165^{\circ}\text{C}$, $V_{CC}(\text{max}) = 24 \text{ V}$, and $I_{CC}(\text{max}) = 4 \text{ mA}$.

Calculate the maximum allowable power level, $P_D(max)$. First, invert equation 3:

$$\Delta T_{max} = T_I(max) - T_A = 165 \,^{\circ}C - 150 \,^{\circ}C = 15 \,^{\circ}C$$

This provides the allowable increase to T_J resulting from internal power dissipation. Then, invert equation 2:

$$P_D(max) = \Delta T_{max} \div R_{\theta IA} = 15^{\circ}C \div 228^{\circ}C/W = 66 \text{ mW}$$

Finally, invert equation 1 with respect to voltage:

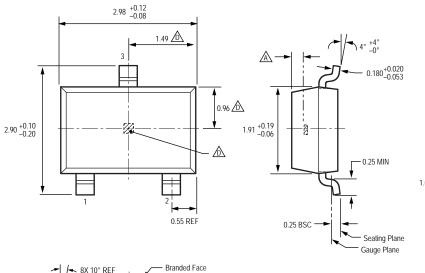
$$V_{CC(est)} = P_D(max) \div I_{CC}(max) = 66 \text{ mW} \div 4 \text{ mA} = 16.5 \text{ V}$$

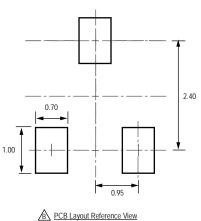
The result indicates that, at T_A , the application and device can dissipate adequate amounts of heat at voltages $\leq V_{CC(est)}$.

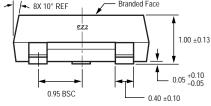
Compare $V_{CC(est)}$ to $V_{CC}(max)$. If $V_{CC(est)} \leq V_{CC}(max)$, then reliable operation between $V_{CC(est)}$ and $V_{CC}(max)$ requires enhanced $R_{\theta JA}$. If $V_{CC(est)} \geq V_{CC}(max)$, then operation between $V_{CC(est)}$ and $V_{CC}(max)$ is reliable under these conditions.

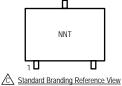


Package LH, 3-Pin (SOT-23W)









For Reference Only; not for tooling use (reference dwg. 802840) Dimensions in millimeters

Dimensions exclusive of mold flash, gate burrs, and dambar protrusions
Exact case and lead configuration at supplier discretion within limits shown

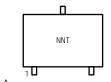
Active Area Depth, 0.28 mm REF

Reference land pattern layout

All pads a minimum of 0.20 mm from all adjacent pads; adjust as necessary to meet application process requirements and PCB layout tolerances

Branding scale and appearance at supplier discretion

hall element, not to scale

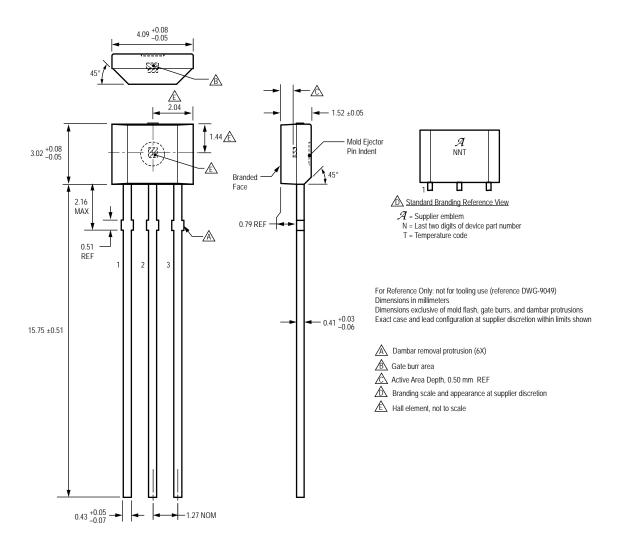


N = Last two digits of device part number T = Temperature code



8

Package UA, 3-Pin SIP



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The products described herein are manufactured under one or more of the following U.S. patents: 5,045,920; 5,264,783; 5,442,283; 5,389,889; 5,581,179; 5,517,112; 5,619,137; 5,621,319; 5,650,719; 5,686,894; 5,694,038; 5,729,130; 5,917,320; and other patents pending.

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